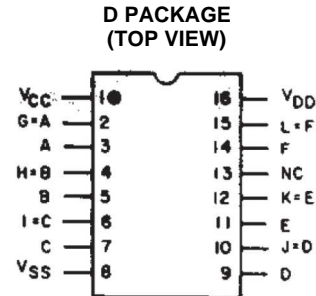


## CMOS HEX BUFFER/CONVERTER

 Check for Samples: [CD4010B-Q1](#)

### FEATURES

- Qualified for Automotive Applications
- 100% Tested for Quiescent Current at 20 V
- Maximum Input Current of 1  $\mu$ A at 18 V Over Full Package-Temperature Range:  
100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V Parametric Ratings
- Latch-Up Performance Meets 100 mA per JESD 78, Class I



### APPLICATIONS

- CMOS to DTL/TTL Hex Converter
- CMOS Current "Sink" or "Source" Driver
- CMOS High-to-Low Logic-Level Converter
- Multiplexer: 1-to-6 or 6-to-1

### DESCRIPTION

CD4010B hex buffer/converter may be used as CMOS to TTL or DTL logic-level converters or CMOS high-sink-current drivers.

The CD4050B is the preferred hex buffer replacement for the CD4010B in all applications except multiplexers. For applications not requiring high sink current or voltage conversion, the CD4069UB hex inverter is recommended.

The CD4010B is supplied in 16-lead hermetic dual-in-line ceramic (D) packages.

### ORDERING INFORMATION<sup>(1)</sup>

T <sub>A</sub>	PACKAGE <sup>(2)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 125°C	SOIC – D	Reel of 2500	CD4010BQDRQ1	CD4010BQ

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at [www.ti.com](http://www.ti.com).

(2) Package drawings, thermal data, and symbolization are available at [www.ti.com/packaging](http://www.ti.com/packaging).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

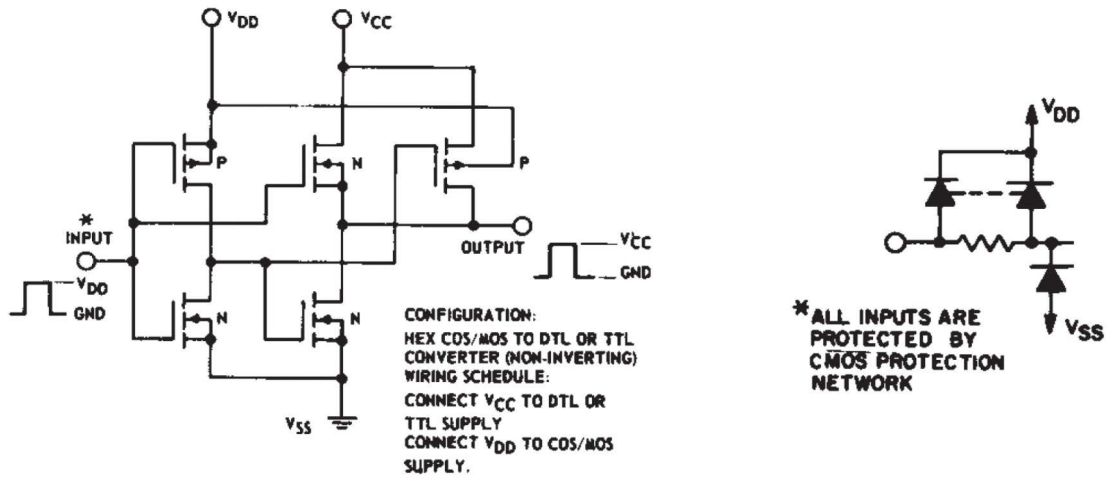
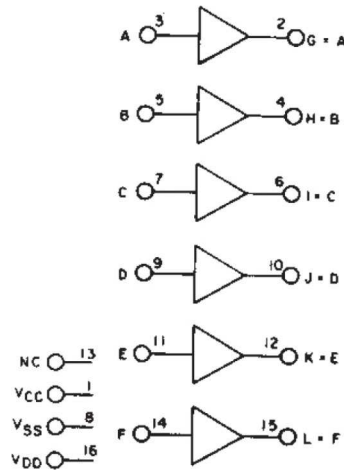


Figure 1. Schematic Diagram – One of Six Identical Stages

Functional Diagram



## ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

		VALUE	UNIT
$V_{DD}$	DC supply voltage range, voltages referenced to $V_{SS}$ terminal	–0.5 to +20	V
	Input voltage range, all inputs	–0.5 to $V_{DD} + 0.5$	V
	DC input current, any one input	±10	mA
$P_D$	Power dissipation per package	$T_A = -40^\circ\text{C}$ to $+100^\circ\text{C}$	500
		$T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$	Derate linearly at 12 mW/°C to 200 mW
	Device dissipation per output transistor	$T_A =$ full package-temperature range (all packages types)	100
$T_A$	Operating temperature range	–40 to +125	°C
$T_{stg}$	Storage temperature range	–65 to +150	°C
	Latch-up performance per JESD 78, Class I	100	mA
ESD	Electrostatic discharge rating <sup>(2)</sup>	Human-body model (HBM)	500
		Machine model (MM)	100
		Charged-Device Model (CDM)	1000

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Tested in accordance with AEC-Q100.

## RECOMMENDED OPERATING CONDITIONS

		MIN	MAX	UNIT
$V_{DD}$	Supply voltage range <sup>(1)</sup>	3	18	V
$V_{CC}$		3	$V_{DD}$	
$V_I$	Input voltage range	$V_{CC}$	$V_{DD}$	V

(1) The CD4010B has high-to-low level voltage conversion capability, but not low-to-high level; therefore, it is recommended that  $V_{DD} > V_I > V_{CC}$ .

## STATIC ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNIT
	V <sub>O</sub>	V <sub>IN</sub>	V <sub>DD</sub>	-40	+85	+125	+25			
							MIN	TYP	MAX	
I <sub>DD</sub> Max Quiescent device current		0, 5	5	1	30	30	0.02			μA
		0, 10	10	2	60	60	0.02			
		0, 15	15	4	120	120	0.02			
		0,20	20	20	600	600	0.04			
I <sub>OL</sub> Min Output low (sink) current	0.4	0, 5	4.5	3.1	2.1	1.8	2.6	3.4		mA
	0.4	0, 5	5	3.6	2.4	2.1	3	4		
	0.5	0, 10	10	9.6	6.4	5.6	8	10		
	1.5	0, 15	15	40	19	16	24	36		
I <sub>OH</sub> Min Output high (source) current	4.6	0, 5	5	-0.23	-0.18	-0.15	-0.2	-0.4		mA
	2.5	0, 5	5	-0.9	-0.65	-0.58	-0.8	-1.6		
	9.5	0, 10	10	-0.5	-0.38	-0.33	-0.45	-0.9		
	13.5	0, 15	15	-1.6	-1.25	-1.1	-1.5	-3		
V <sub>OL</sub> Max Output voltage: Low-level		0, 5	5	0.05			0	0.05		V
		0, 10	10	0.05			0	0.05		
		0, 15	15	0.05			0	0.05		
V <sub>OH</sub> Min Output voltage: High-level		0, 5	5	4.95			4.95	5		V
		0, 10	10	9.95			9.95	10		
		0, 15	15	14.95			14.95	15		
V <sub>IL</sub> Max Input low voltage	0.5		5	1.5				1.5		V
	1		10	3				3		
	1.5		15	4				4		
V <sub>IH</sub> Min Input high voltage	4.5		5	3.5			3.5		V	
	9		10	7			7			
	13.5		15	11			11			
I <sub>IN</sub> Max Input current		0, 18	18	±0.1	±1	±1	±10 <sup>-5</sup>		±0.1	μA

**DYNAMIC ELECTRICAL CHARACTERISTICS**
 $T_A = 25^\circ\text{C}$ , Input  $t_r/t_f = 20\text{ ns}$ ,  $C_L = 50\text{ pf}$ ,  $R_L = 200\text{ k}\Omega$ 

PARAMETER	TEST CONDITIONS			LIMITS ALL PKGS		UNIT
	$V_{DD}$ (V)	$V_I$ (V)	$V_{CC}$ (V)	TYP	MAX	
$t_{PLH}$ Propagation delay time: low-to-high	5	5	5	100	200	ns
	10	10	10	50	100	
	10	10	5	50	100	
	15	15	15	35	70	
	15	15	5	35	70	
$t_{PHL}$ Propagation time: high-to-low	5	5	5	65	130	ns
	10	10	10	35	70	
	10	10	5	30	70	
	15	15	15	25	50	
	15	15	5	20	40	
$t_{TLH}$ Transition time: low-to-high	5	5	5	150	350	ns
	10	10	10	75	150	
	15	15	15	55	110	
$t_{THL}$ Transition time: high-to-low	5	5	5	35	90	ns
	10	10	10	20	45	
	15	15	15	15	40	
$C_{IN}$ Input capacitance				5	7.5	pF

TYPICAL CHARACTERISTICS

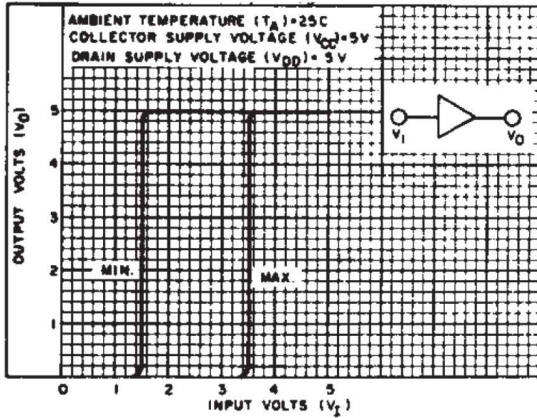


Figure 2. Minimum and Maximum Voltage Transfer Characteristics ( $V_{DD} = 5\text{ V}$ )

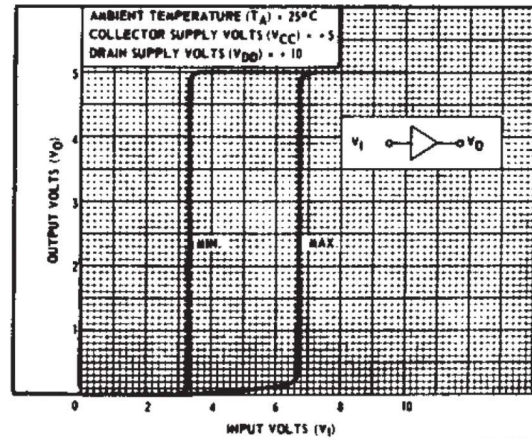


Figure 3. Minimum and Maximum Voltage Transfer Characteristics ( $V_{DD} = 10\text{ V}$ )

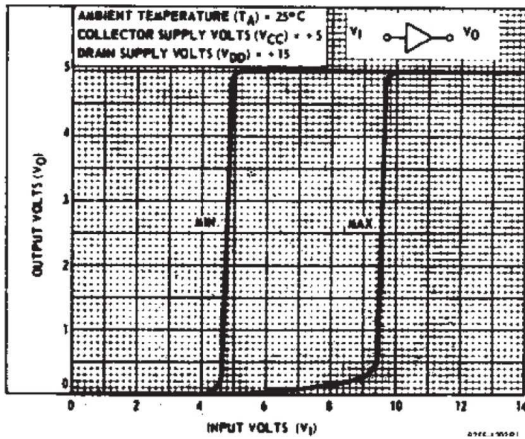


Figure 4. Minimum and Maximum Voltage Transfer Characteristics ( $V_{DD} = 15\text{ V}$ )

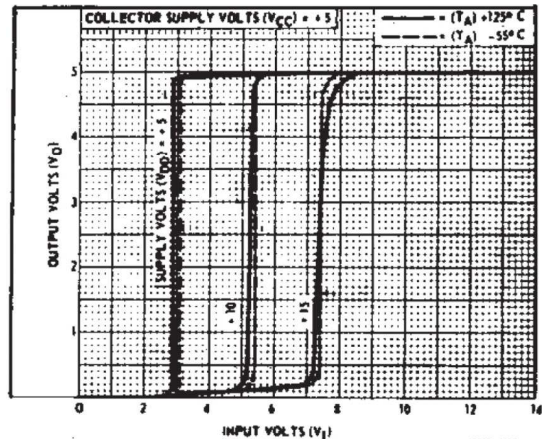


Figure 5. Typical Voltage Transfer Characteristics as a Function of Temperature

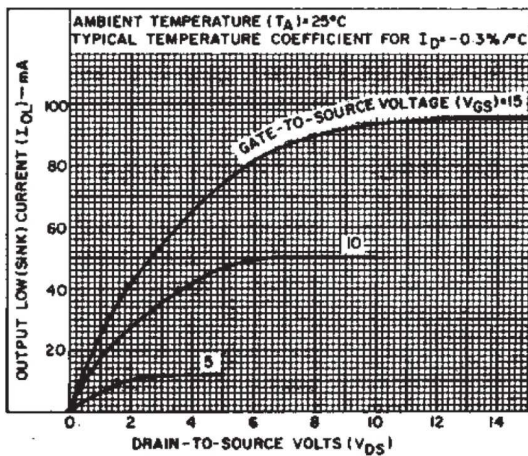


Figure 6. Typical Output Low (Sink) Current Characteristics

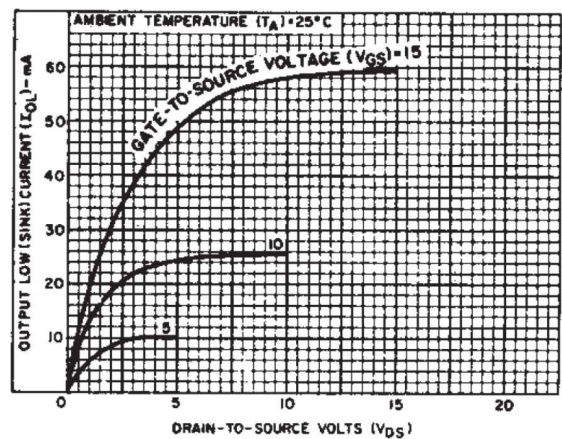


Figure 7. Minimum Output Low (Sink) Current Characteristics



TYPICAL CHARACTERISTICS (continued)

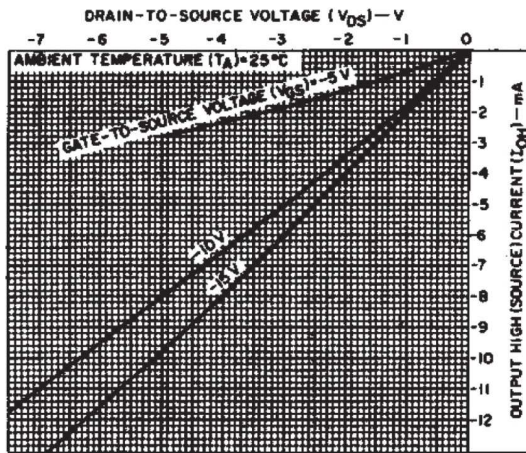


Figure 8. Typical Output High (Source) Current Characteristics

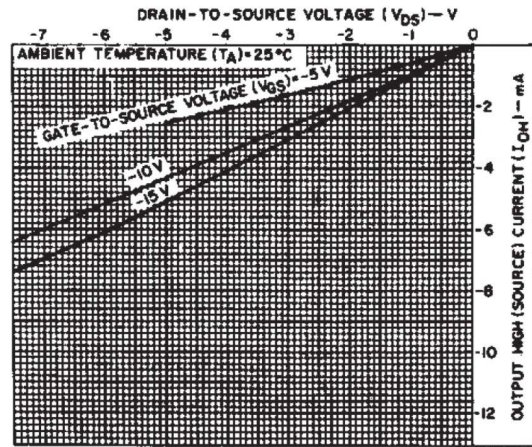


Figure 9. Minimum Output High (Source) Current Characteristics

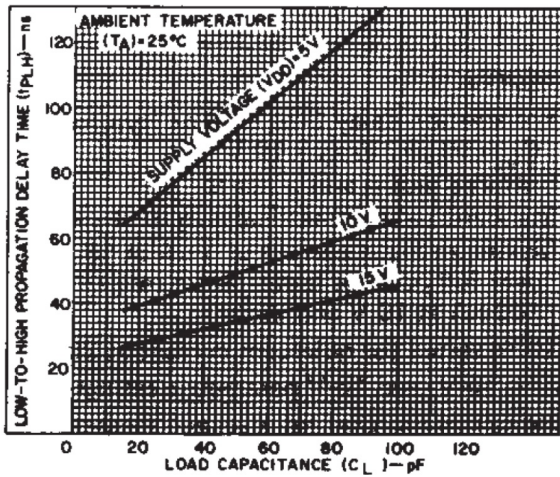


Figure 10. Typical Low-to-High Propagation Delay Time vs Load Capacitance

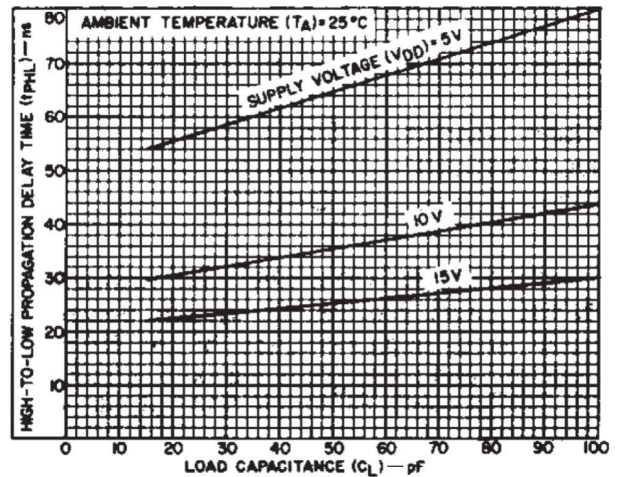


Figure 11. Typical High-to-Low Propagation Delay Time vs Load Capacitance

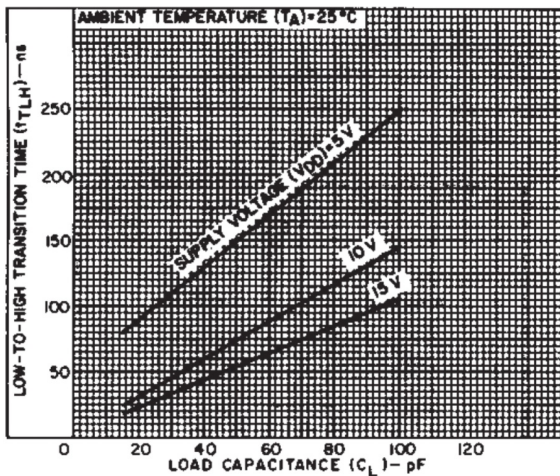


Figure 12. Typical Low-to-High Transition Time vs Load Capacitance

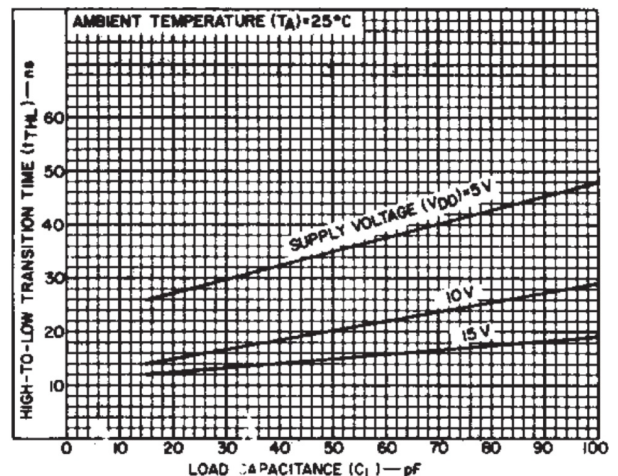


Figure 13. Typical High-to-Low Transition Time vs Load Capacitance

**TYPICAL CHARACTERISTICS (continued)**

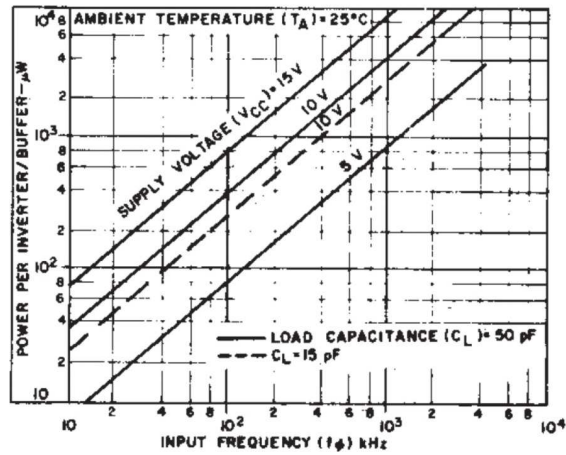


Figure 14. Typical Dissipation Characteristics



PARAMETER MEASUREMENT INFORMATION

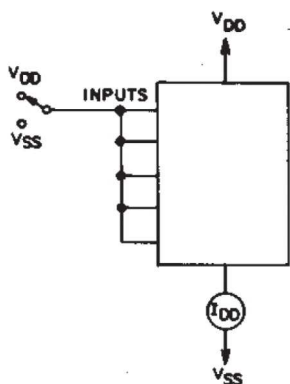


Figure 15. Quiescent Device Current Test Circuit

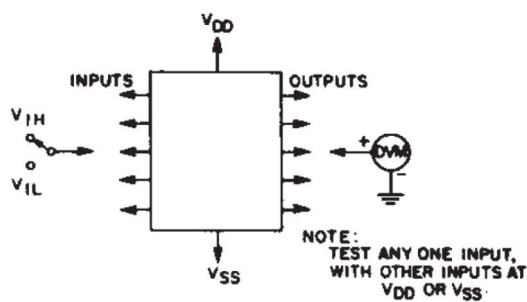
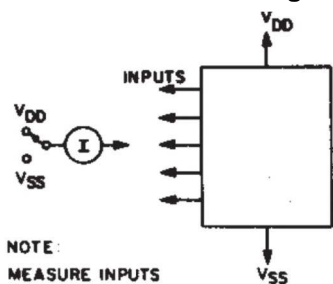
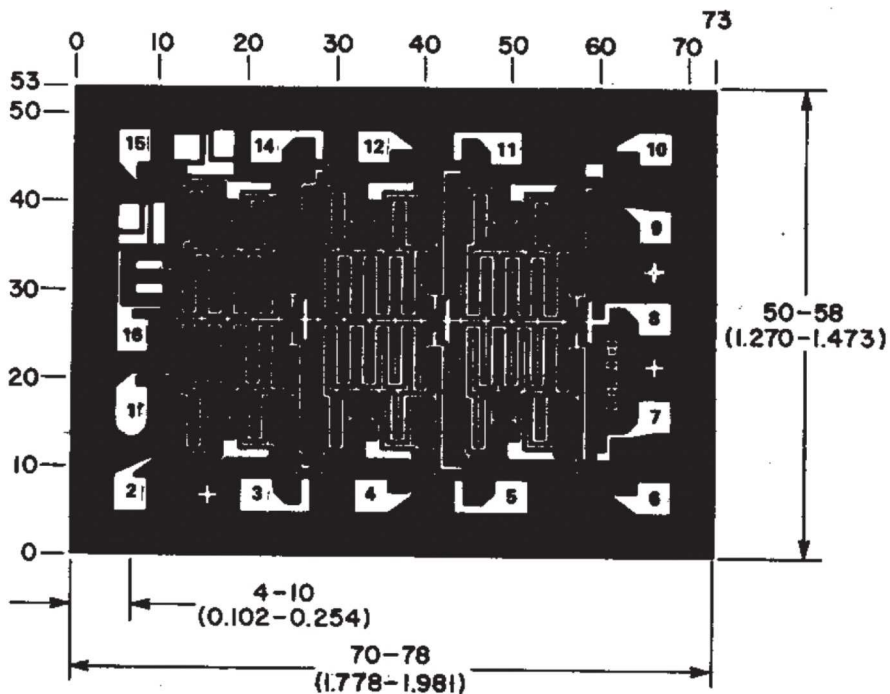


Figure 16. Noise Immunity Test Circuit



NOTE:  
MEASURE INPUTS  
SEQUENTIALLY,  
TO BOTH V<sub>DD</sub> AND V<sub>SS</sub>.  
CONNECT ALL UNUSED  
INPUTS TO EITHER  
V<sub>DD</sub> OR V<sub>SS</sub>.

Figure 17. Input Current Test Circuit



Note: Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduation are in mils ( $10^{-3}$  inch).

Figure 18. Dimensions and Layout

## REVISION HISTORY

Changes from Original (March 2010) to Revision A	Page
• Changed STATIC ELECTRICAL CHARACTERISTICS table to correct typos and misplaced data .....	4

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">CD4010BQDRQ1</a>	Active	Production	SOIC (D)   16	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CD4010BQ
CD4010BQDRQ1.A	Active	Production	SOIC (D)   16	2500   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CD4010BQ

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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**OTHER QUALIFIED VERSIONS OF CD4010B-Q1 :**

- Catalog : [CD4010B](#)

- Military : [CD4010B-MIL](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AC.

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Last updated 10/2025